



# PJT7800

## 20V N-Channel Enhancement Mode MOSFET – ESD Protected

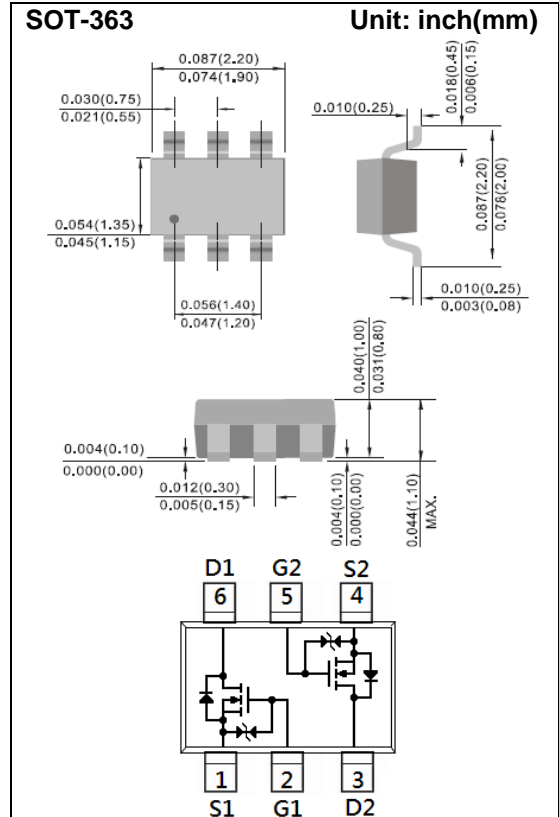
<b>Voltage</b>	<b>20 V</b>	<b>Current</b>	<b>1A</b>
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### Features

- RDS(ON) , VGS@4.5V, ID@1.0A<150mΩ
- RDS(ON) , VGS@2.5V, ID@0.7A<215mΩ
- RDS(ON) , VGS@1.8V, ID@0.3A<400mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std.(Halogen Free)

### Mechanical Data

- Case : SOT-363 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0002 ounces, 0.006 grams
- Marking : T00



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±8	V
Continuous Drain Current	I <sub>D</sub>	1	A
Pulsed Drain Current (Note 4)	I <sub>DM</sub>	4	A
Power Dissipation	T <sub>a</sub> =25°C	350	mW
	Derate above 25°C	2.8	mW/°C
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~150	°C
Typical Thermal resistance	R <sub>θJA</sub>	357	°C/W
- Junction to Ambient (Note 3)			



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## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.8	1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=1A$	-	120	150	m $\Omega$
		$V_{GS}=2.5V, I_D=0.7A$	-	160	215	
		$V_{GS}=1.8V, I_D=0.3A$	-	260	400	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$	-	0.01	1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 8V, V_{DS}=0V$	-	$\pm 2$	$\pm 10$	$\mu A$
<b>Dynamic</b> (Note 5)						
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=1A,$ $V_{GS}=4.5V$ (Note 1,2)	-	1.6	-	nC
Gate-Source Charge	$Q_{gs}$		-	0.31	-	
Gate-Drain Charge	$Q_{gd}$		-	0.41	-	
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V,$ $f=1.0MHz$	-	92	-	pF
Output Capacitance	$C_{oss}$		-	25	-	
Reverse Transfer Capacitance	$C_{rss}$		-	9.1	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A,$ $V_{GS}=4.5V,$ $R_G=6\Omega$ (Note 1,2)	-	5.8	-	ns
Turn-On Rise Time	$t_r$		-	25.8	-	
Turn-Off Delay Time	$t_{d(off)}$		-	42	-	
Turn-Off Fall Time	$t_f$		-	32	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_S$	---	-	-	1	A
Diode Forward Voltage	$V_{SD}$	$I_S=1.0A, V_{GS}=0V$		0.85	1.2	V

**NOTES :**

1. Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
4. The maximum current rating is package limited
5. Guaranteed by design, not subject to production testing.



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## TYPICAL CHARACTERISTIC CURVES

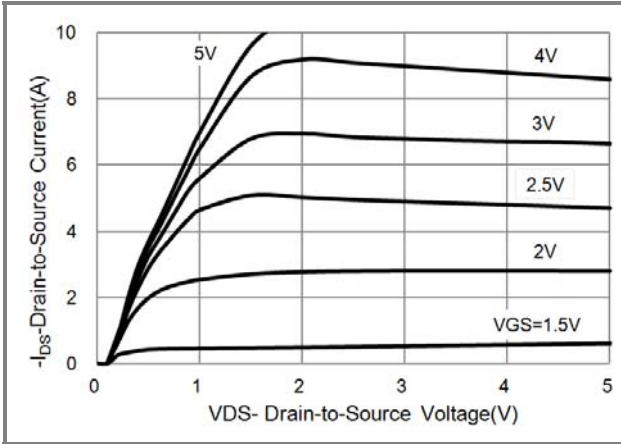


Fig.1 On-Region Characteristics

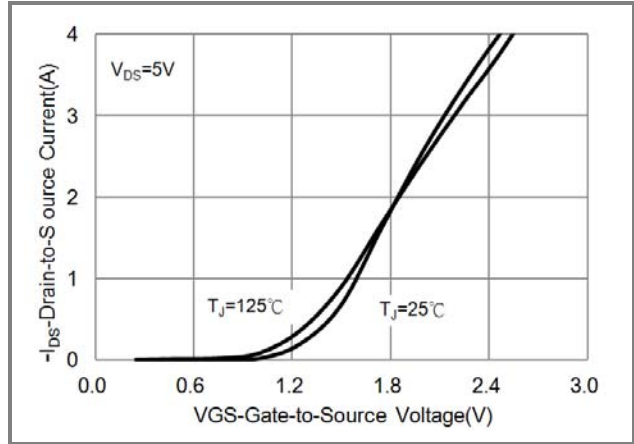


Fig.2 Transfer Characteristics

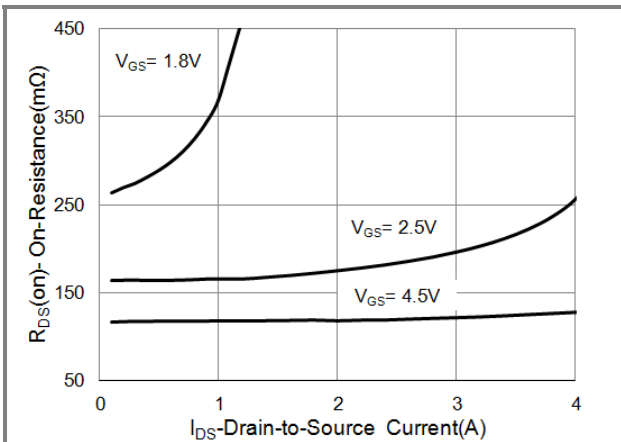


Fig.3 On-Resistance vs. Drain Current

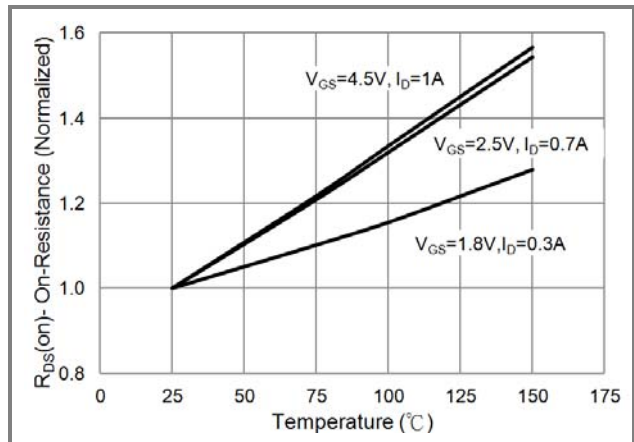


Fig.4 On-Resistance vs. Junction temperature

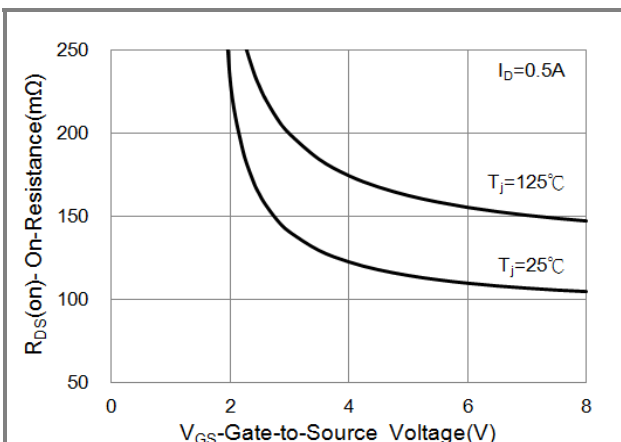


Fig.5 On-Resistance Variation with V\_GS.

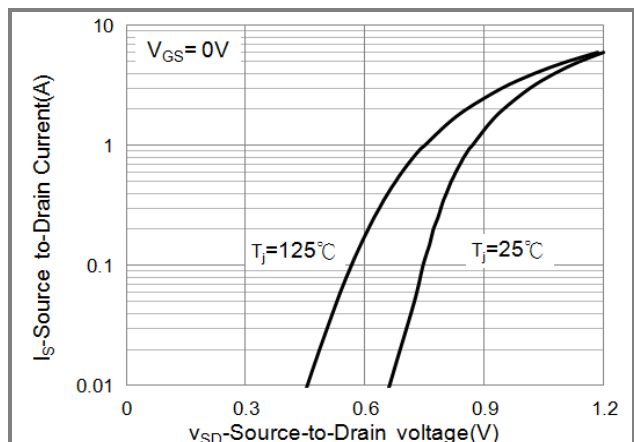


Fig.6 Body Diode Characteristics



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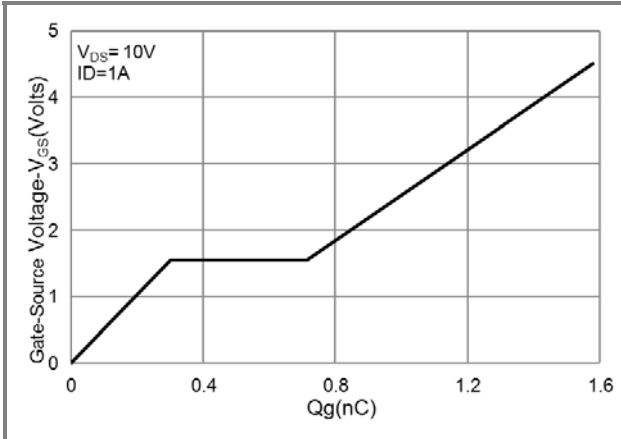


Fig.7 Gate-Charge Characteristics

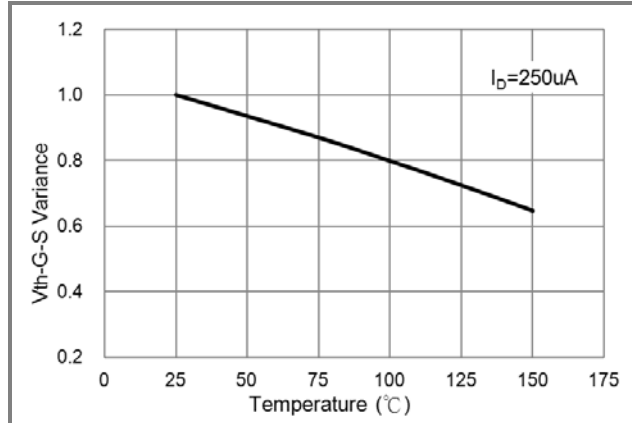


Fig.8 Threshold Voltage Variation with Temperature.

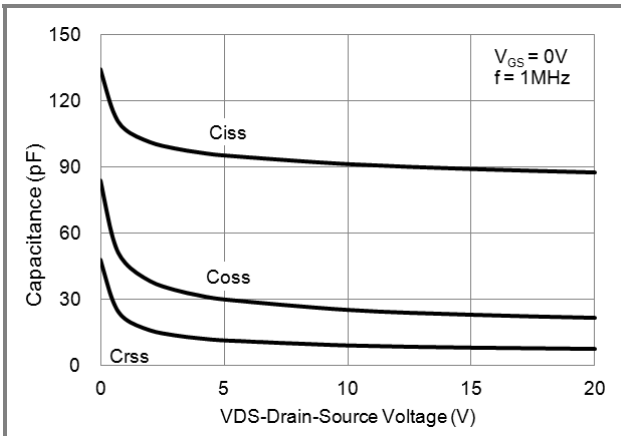


Fig.9 Capacitance vs. Drain-Source Voltage.

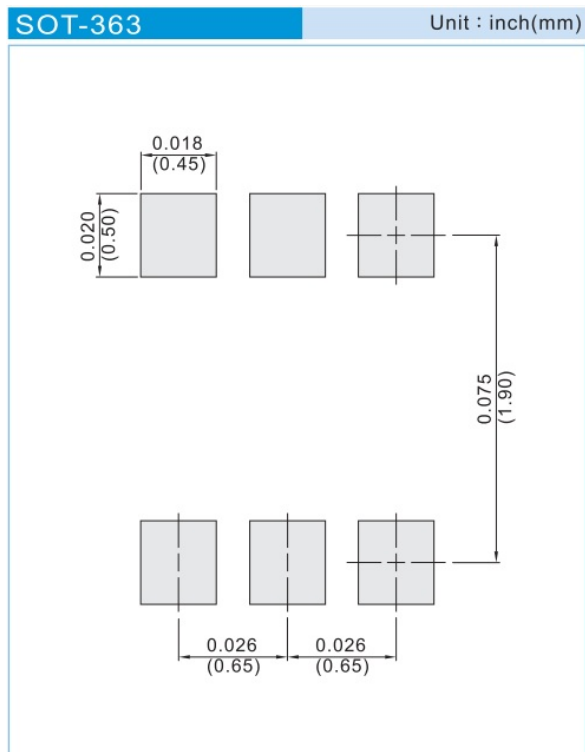


# PJT7800

## PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJT7800_R1_00001	SOT-363	3K pcs / 7" reel	T00	Halogen free
PJT7800_R2_00001	SOT-363	10K pcs / 13" reel	T00	Halogen free

## MOUNTING PAD LAYOUT





## PJT7800

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